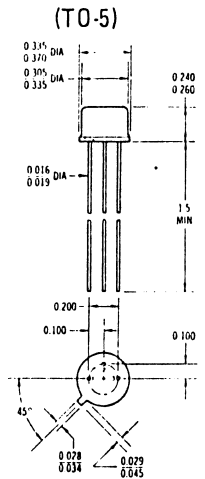


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N-P-N SILICON TRANSISTOR

absolute maximum ratings: (25°C) (unless otherwise specified)

Voltages		
Collector to Emitter	V_{CE0}	30 volts
Emitter to Base	V_{EB0}	4 volts
Collector to Base	V_{CB0}	30 volts



All JEDEC dimensions and notes apply



PIN 1: EMITTER
PIN 2: BASE
PIN 3: COLLECTOR

DIMENSIONS ARE IN INCHES
UNLESS OTHERWISE NOTED.

electrical characteristics: (25°C) (unless otherwise specified)

	Min.	Typ.	Max.
Collector Cutoff Current ($V_{CB} = 18V$) ($V_{CB} = 18V, T_A = 100^\circ C$)	I_{CBO}		0.5 μA
Collector-Emitter Breakdown Voltage ($I_C = 1mA$)	BV_{CEO}	30	15 μA
Emitter-Base Breakdown Voltage ($I_E = 500 \mu A$)	BV_{EBO}	4	volts
Forward Current Transfer Ratio ($V_{CE} = 4.5V, I_C = 2mA$)	h_{FE}	20	100
Collector Saturation Voltage ($I_C = 10mA, I_B = 1mA$)	$V_{CE(SAT)}$		1 volt

